

Fig. 1.

Growth of multiple non-compositional-graded layers

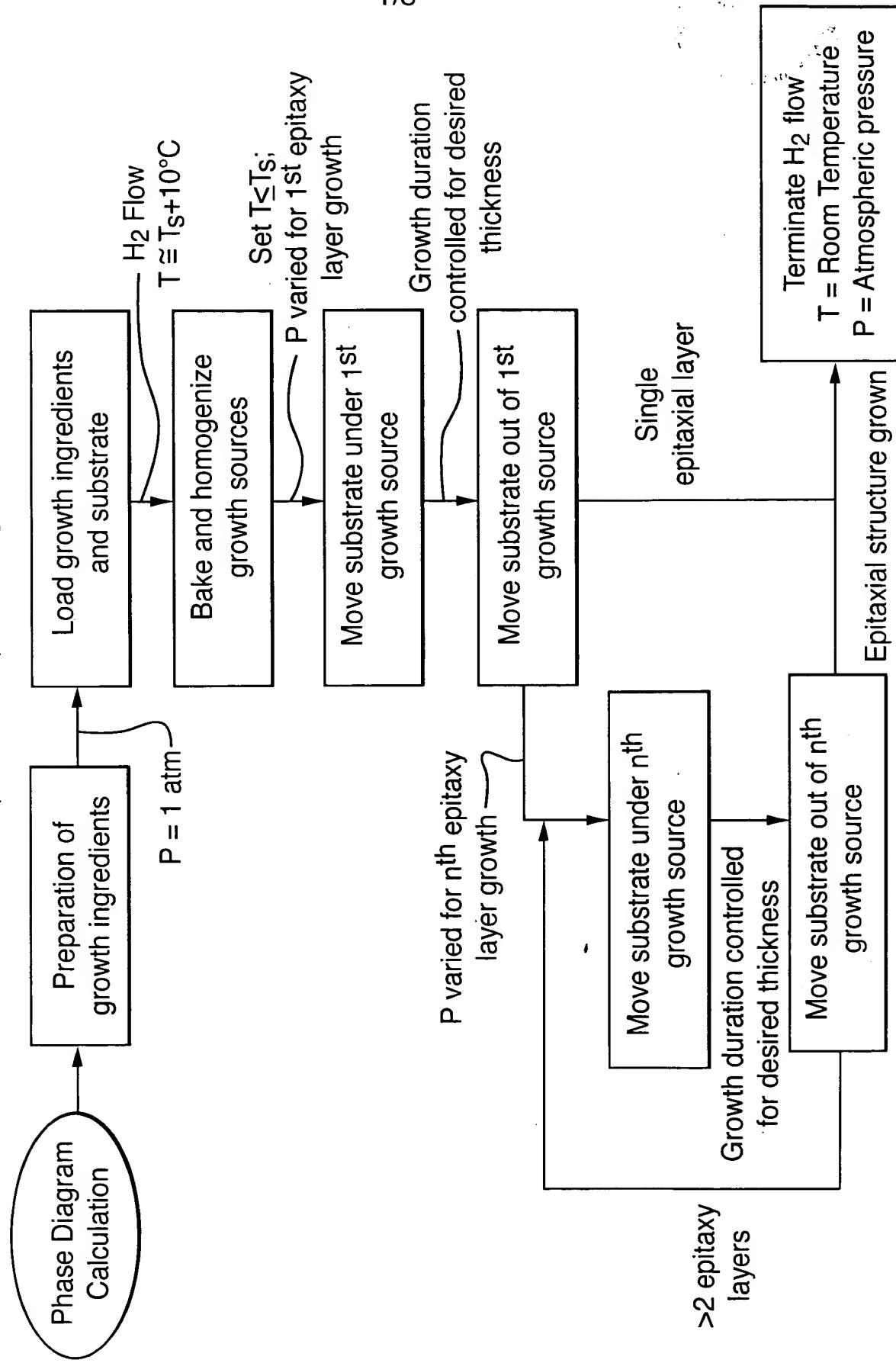
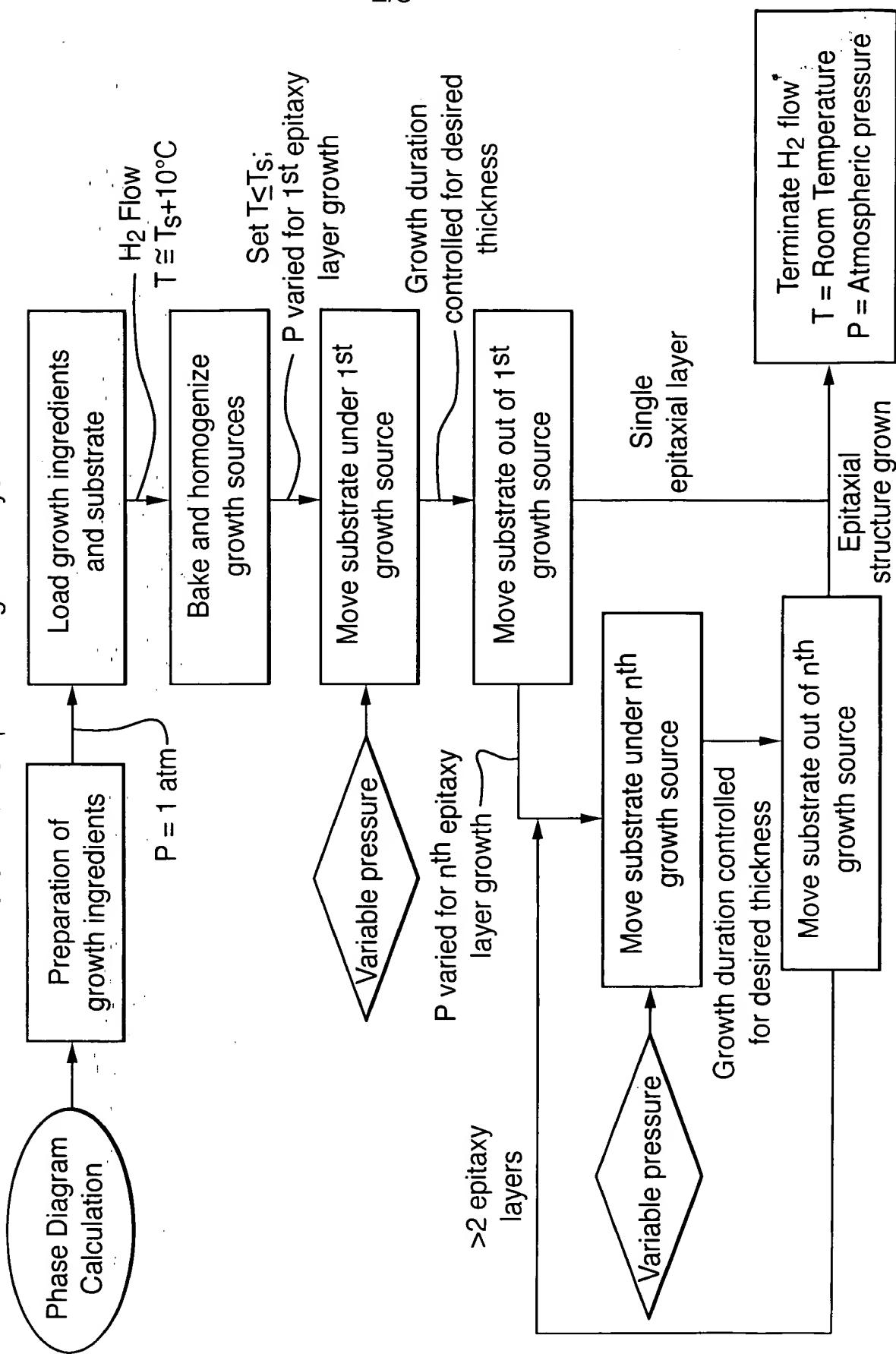


Fig.2.

Growth of compositional-graded layer



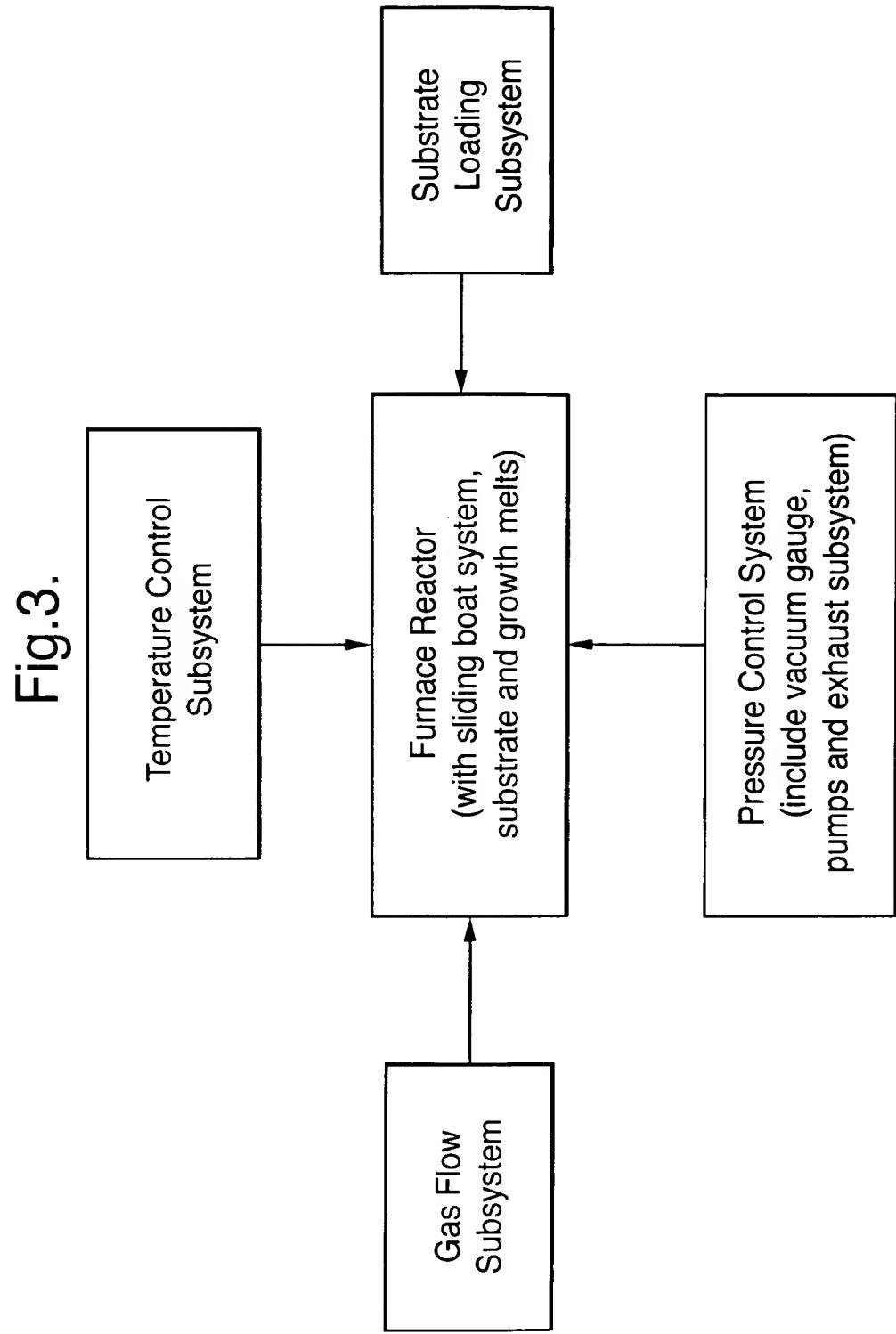
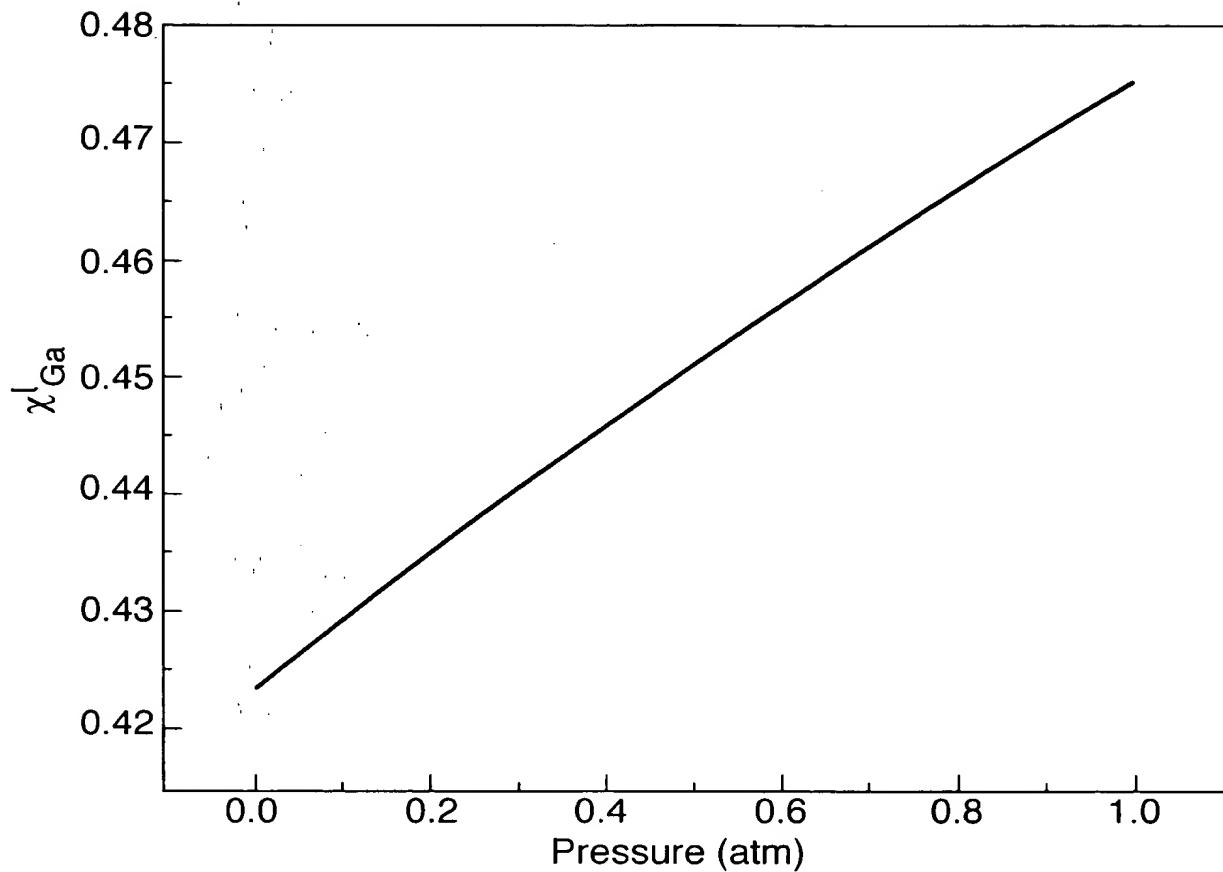
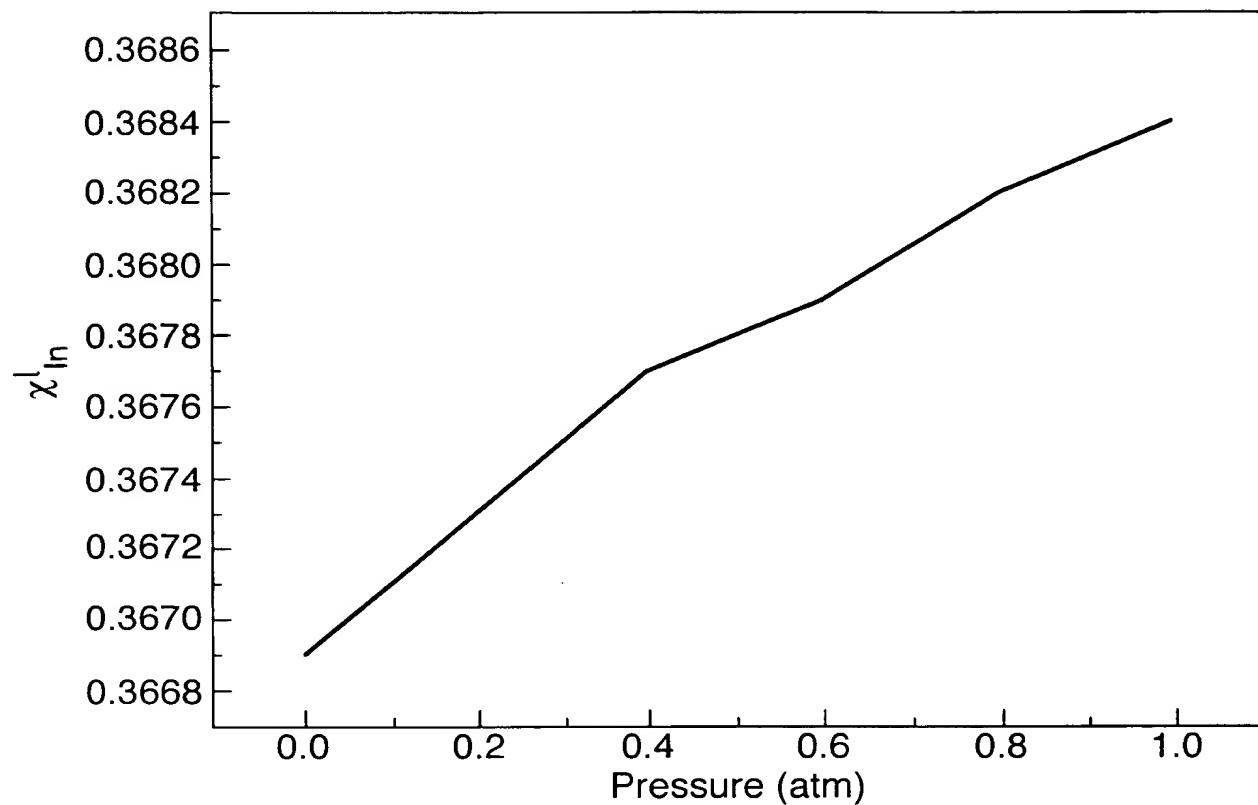


Fig.4.



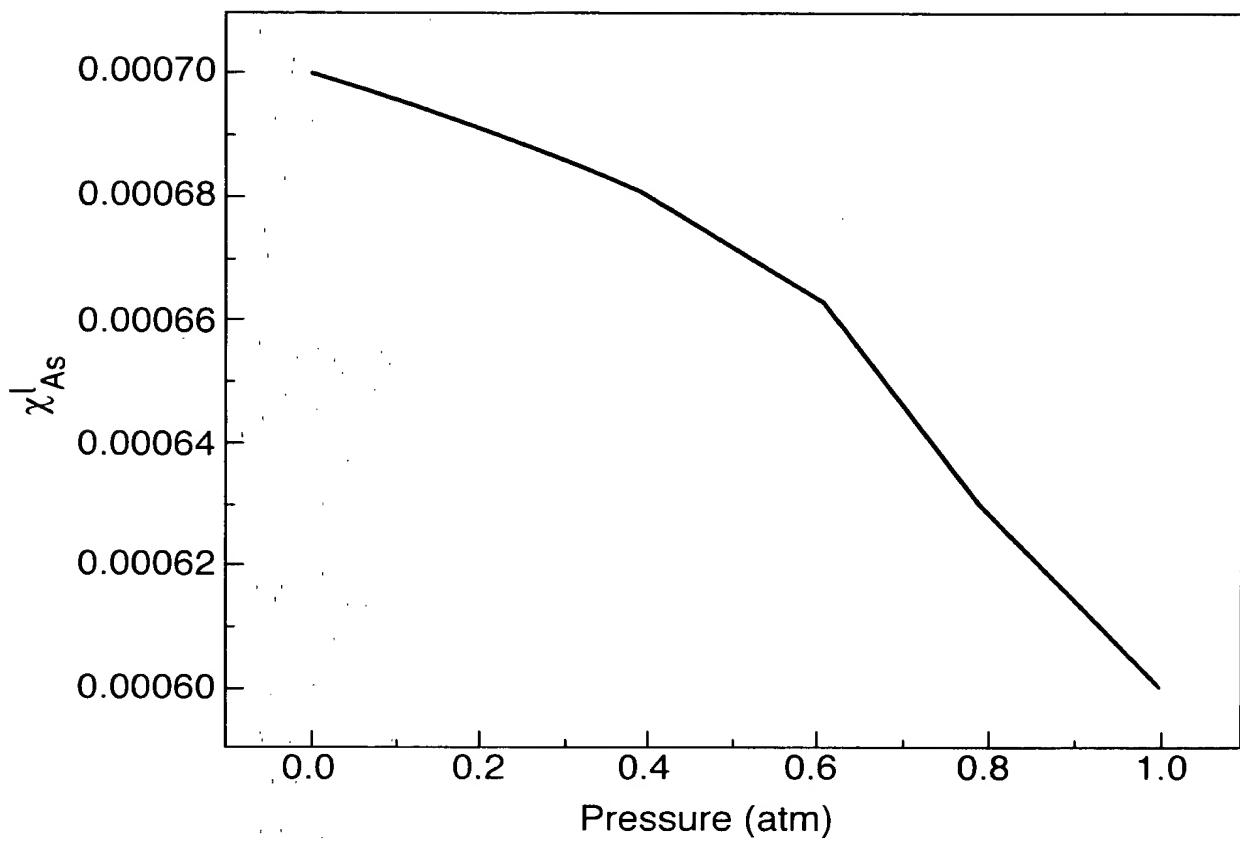
Atomic fraction χ_{Ga}^l in melt for $\text{In}_{0.1}\text{Ga}_{0.9}\text{As}_{0.087}\text{Sb}_{0.913}$ growth on GaSb (100) substrate at 550°C as a function of pressure.

Fig.5.



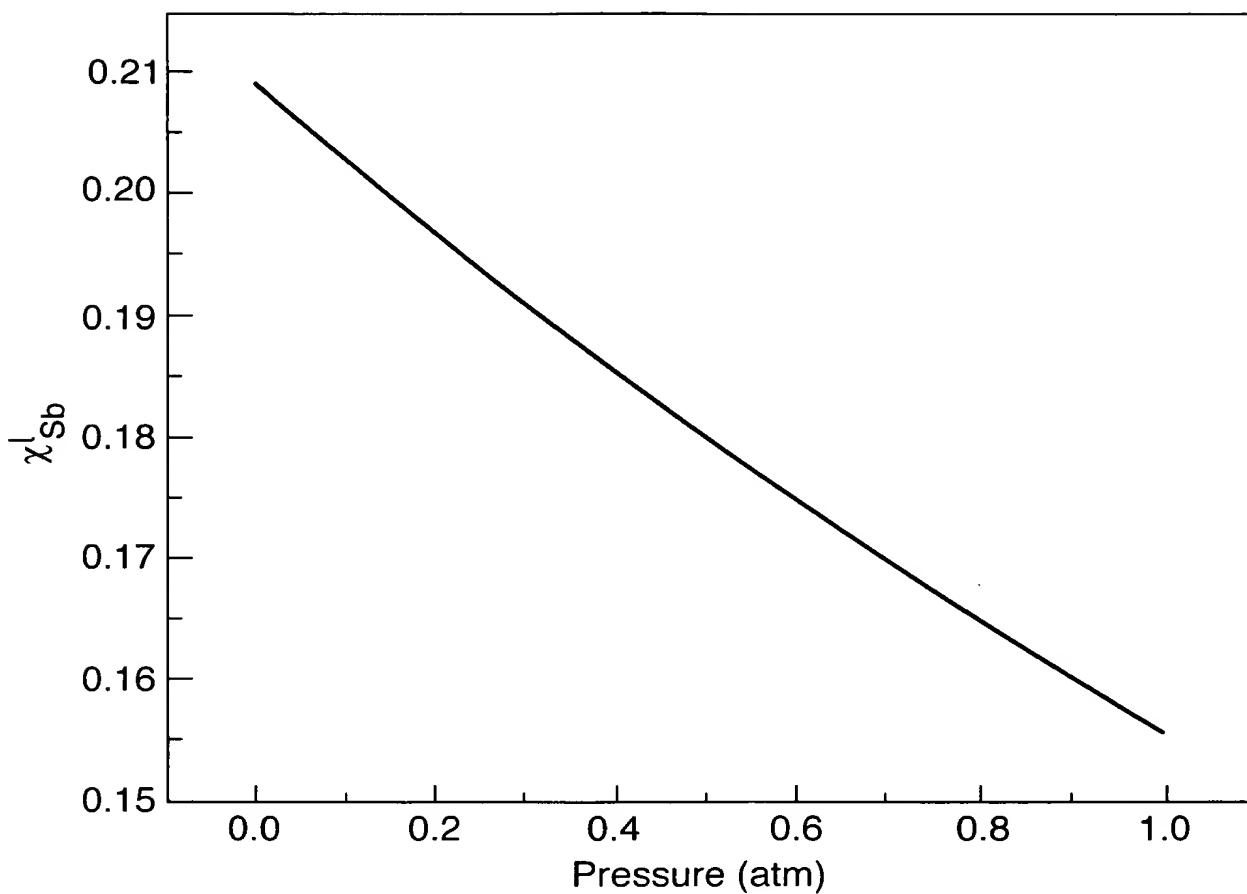
Atomic fraction χ_{In} in melt for $\text{In}_{0.1}\text{Ga}_{0.9}\text{As}_{0.087}\text{Sb}_{0.913}$ growth on GaSb (100) substrate at 550°C as a function of pressure.

Fig.6.



Atomic fraction χ_{As}^l in melt for $In_{0.1}Ga_{0.9}As_{0.087}Sb_{0.913}$ growth on GaSb (100) substrate at 550°C as a function of pressure.

Fig.7.



Atomic fraction χ_{Sb}^l in melt for $\text{In}_{0.1}\text{Ga}_{0.9}\text{As}_{0.087}\text{Sb}_{0.913}$ growth on GaSb (100) substrate at 550°C as a function of pressure.

Fig.8(a).

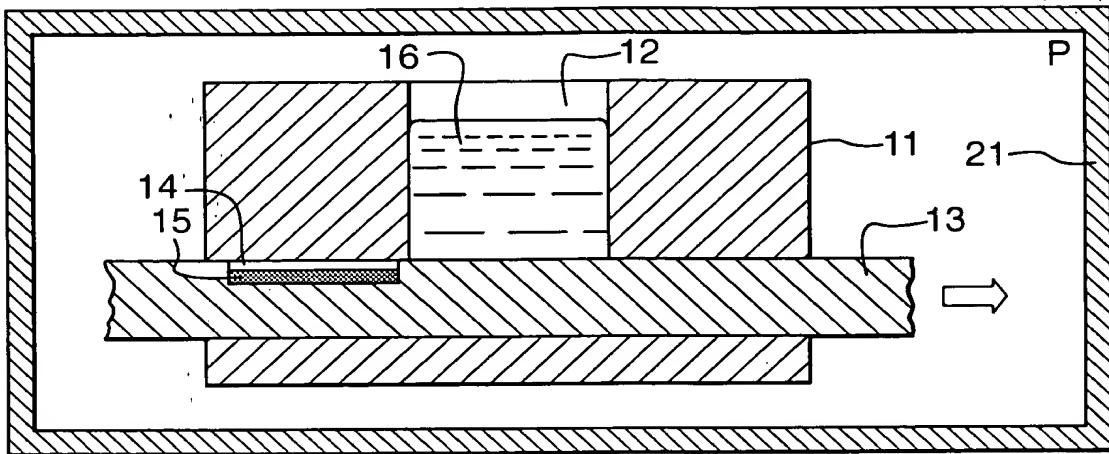


Fig.8(b).

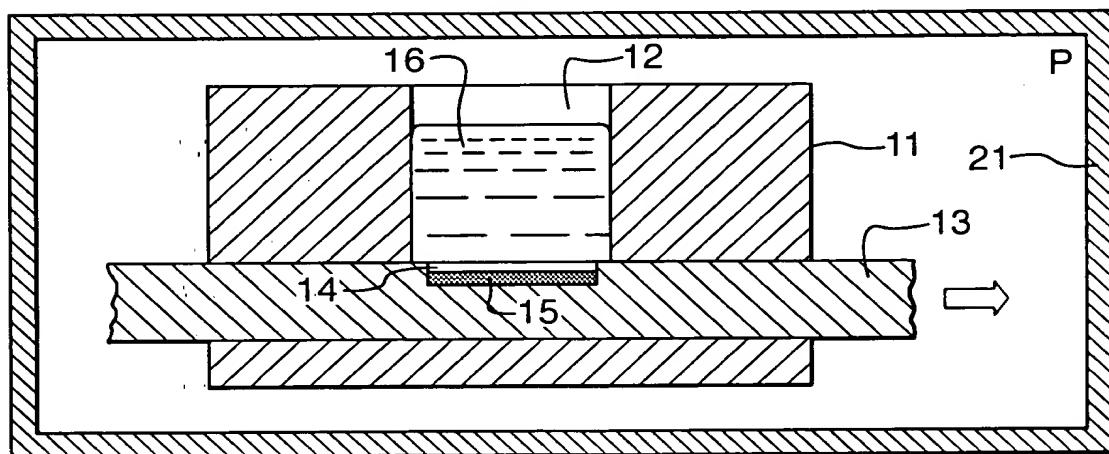


Fig.8(c).

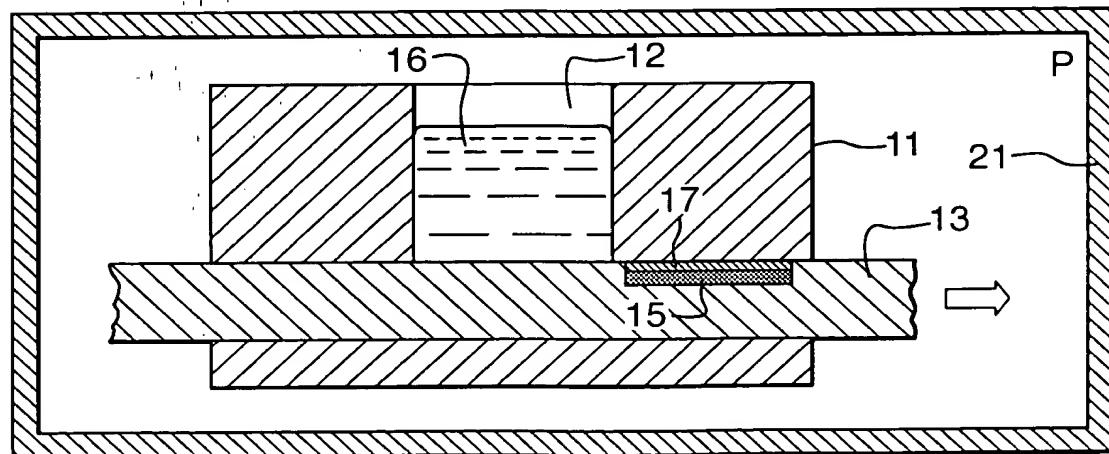


FIGURE 1

Growth of multiple non-compositional-graded layers

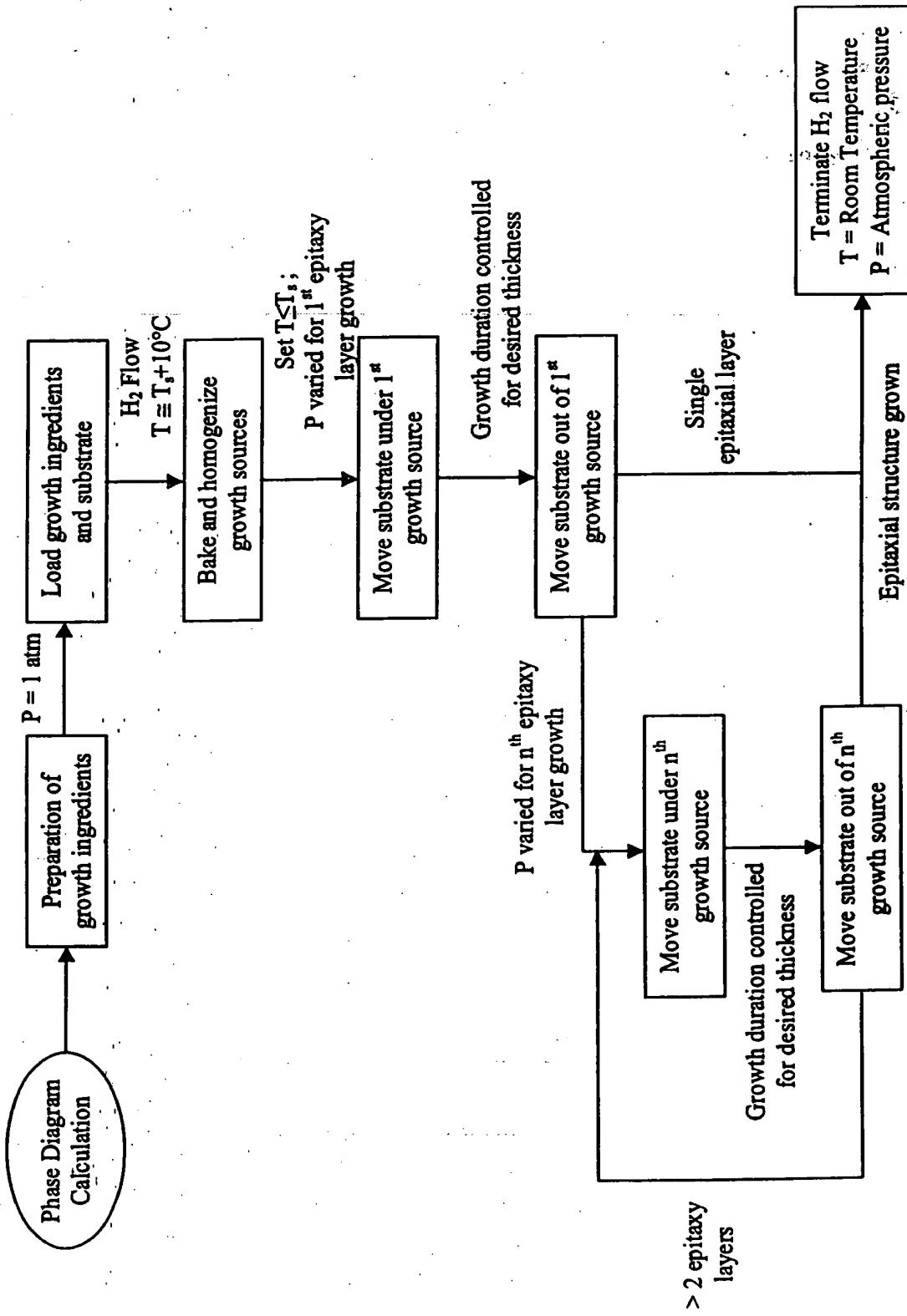
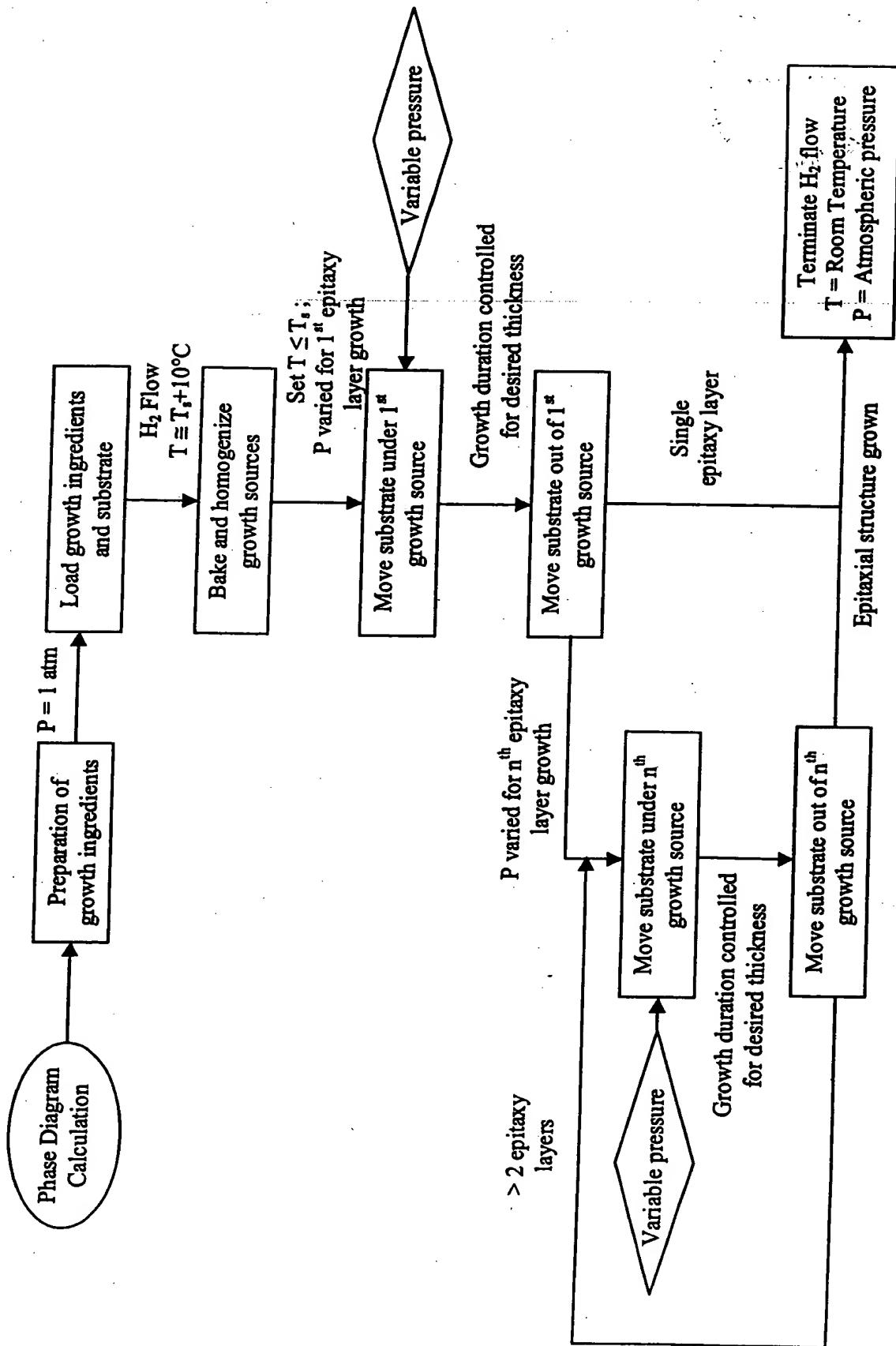


FIGURE 2
Growth of compositional-graded layer



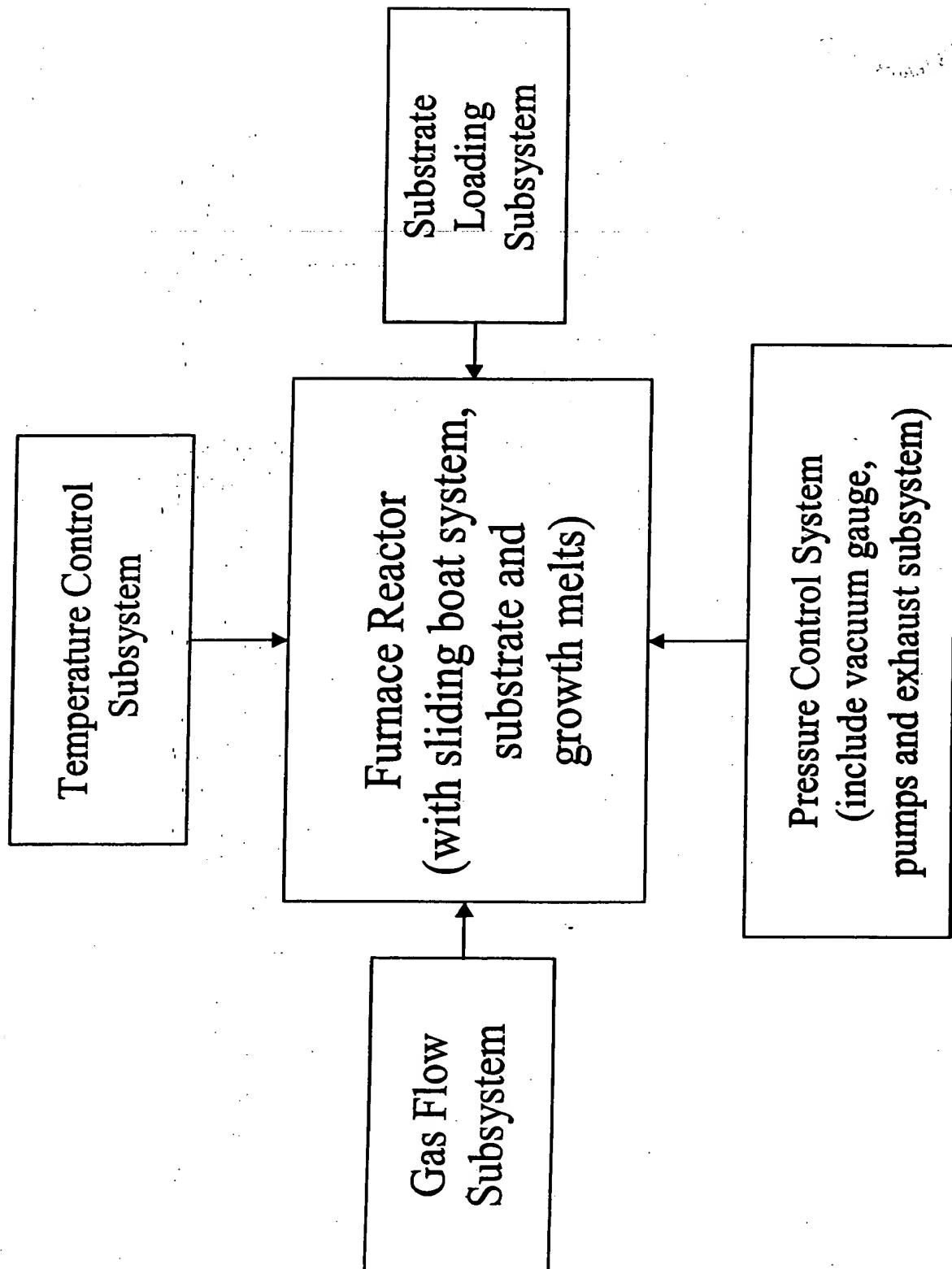
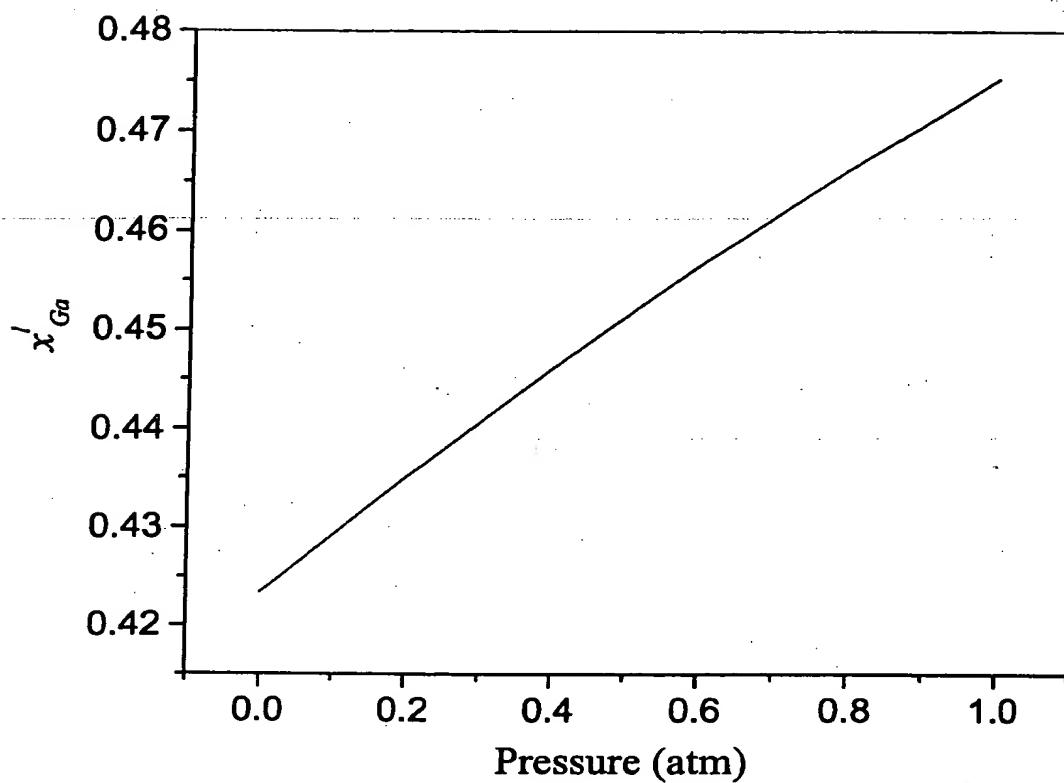


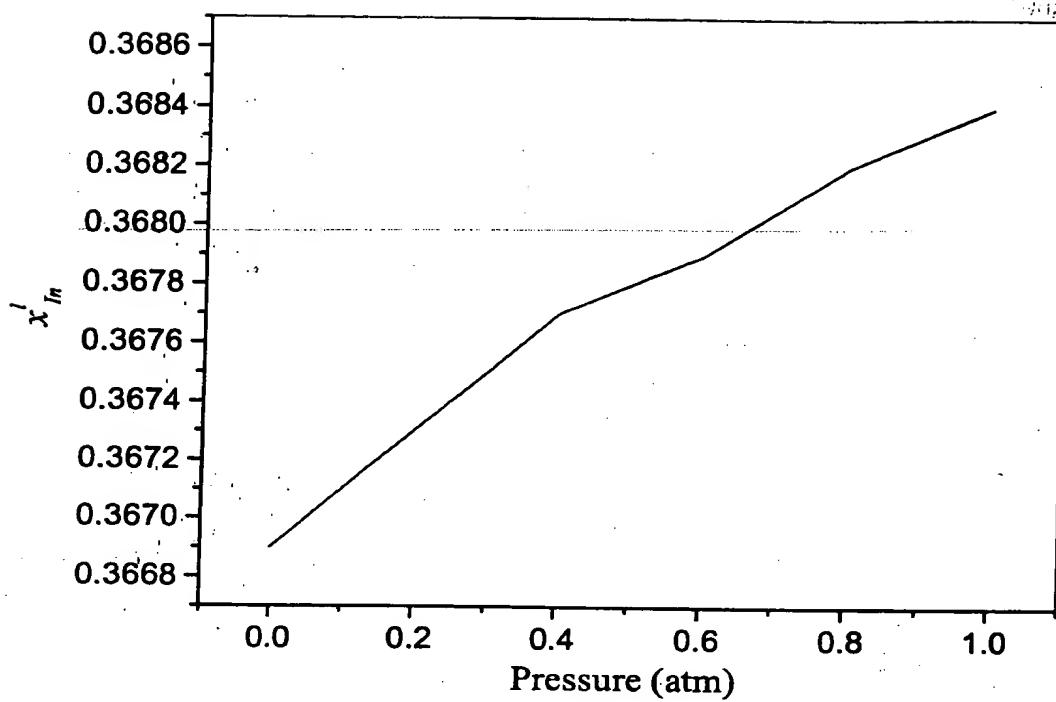
FIGURE 3.

FIGURE 4



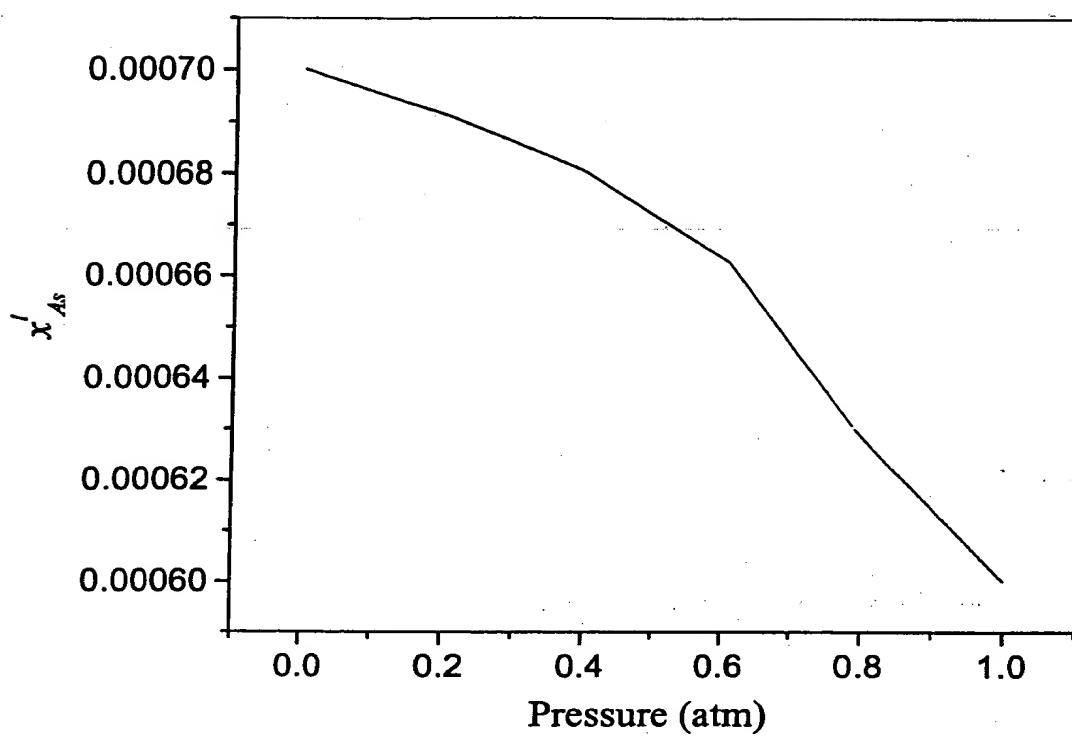
Atomic fraction x'_{Ga} in melt for $In_{0.1}Ga_{0.9}As_{0.087}Sb_{0.913}$ growth on
GaSb (100) substrate at 550 °C as a function of pressure.

FIGURE 5



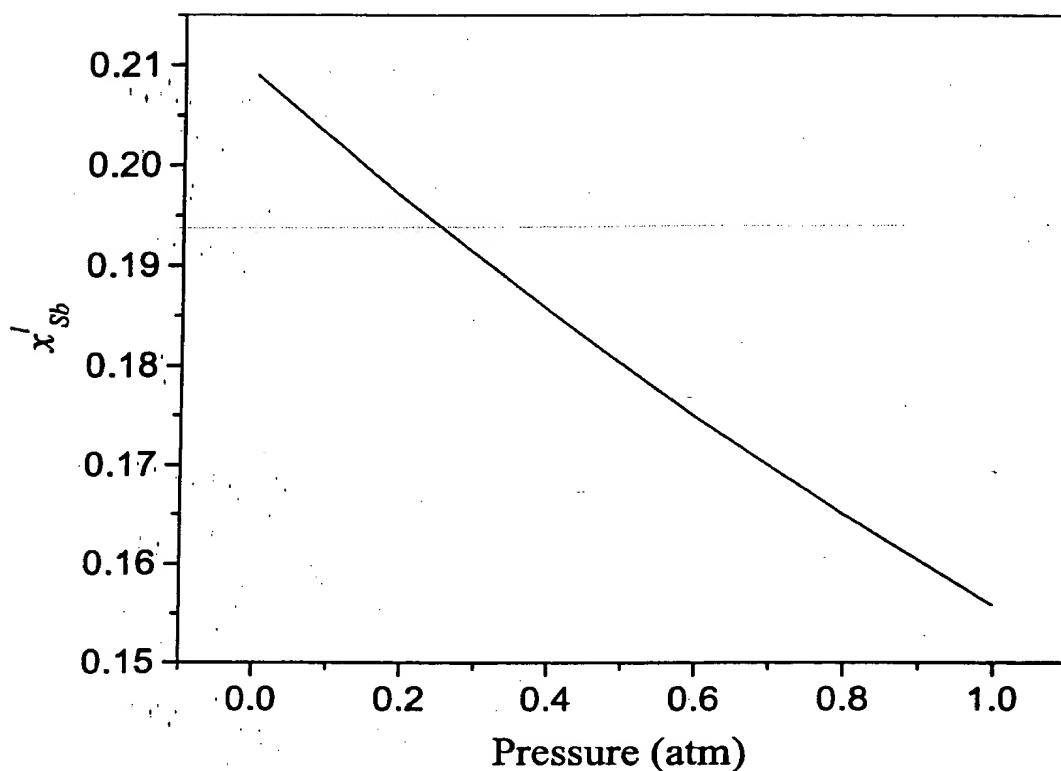
Atomic fraction x'_{In} in melt for $In_{0.1}Ga_{0.9}As_{0.087}Sb_{0.913}$ growth on
GaSb (100) substrate at 550 °C as a function of pressure.

FIGURE 6



Atomic fraction x'_{As} in melt for $In_{0.1}Ga_{0.9}As_{0.087}Sb_{0.913}$ growth on
GaSb (100) substrate at 550 °C as a function of pressure.

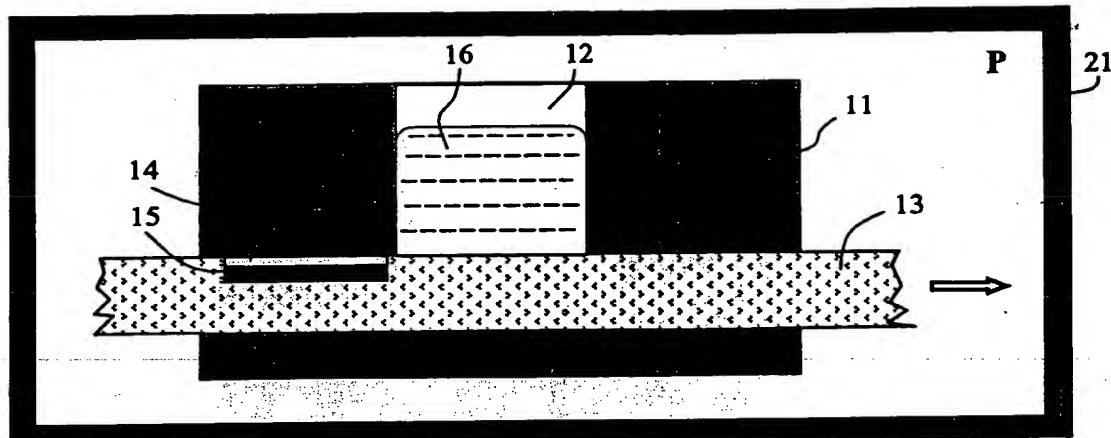
FIGURE 7



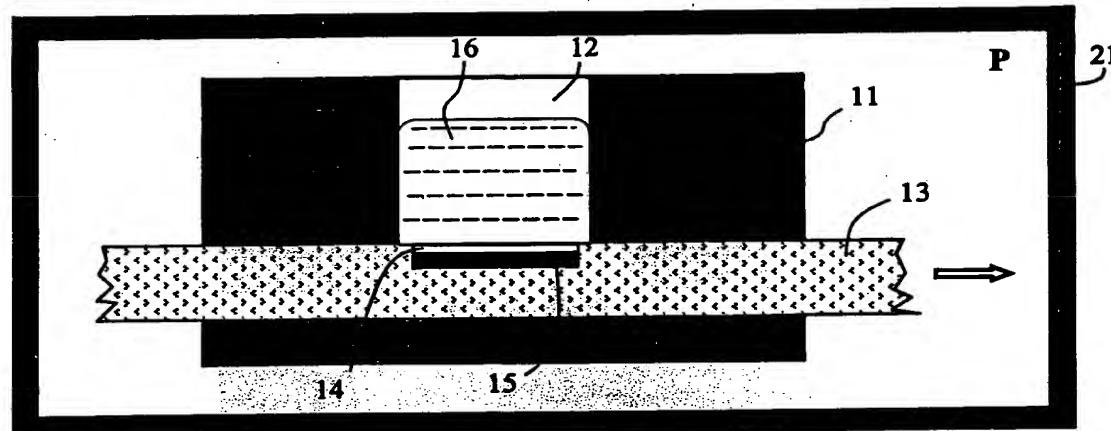
Atomic fraction x'_Sb in melt for $In_{0.1}Ga_{0.9}As_{0.087}Sb_{0.913}$ growth on
GaSb (100) substrate at 550 °C as a function of pressure.

FIGURE 8

(a)



(b)



(c)

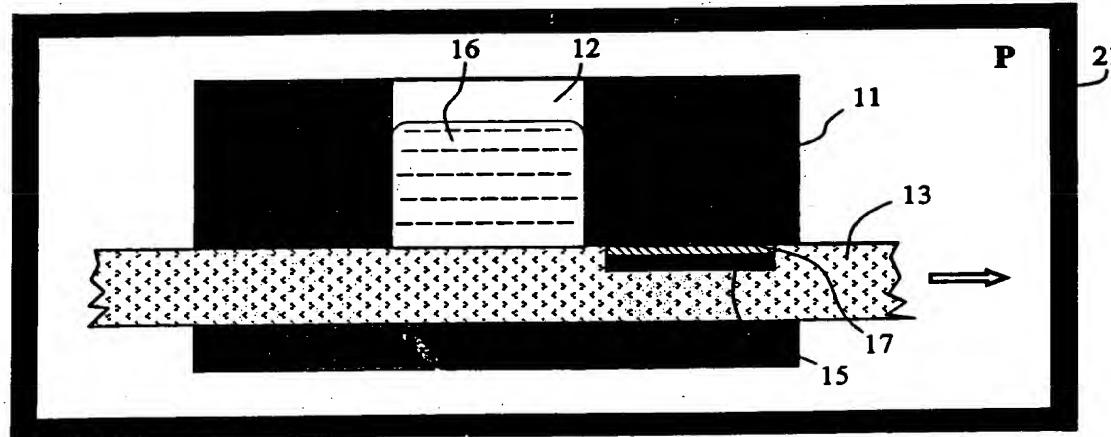


FIGURE 1

Growth of multiple non-compositional-graded layers

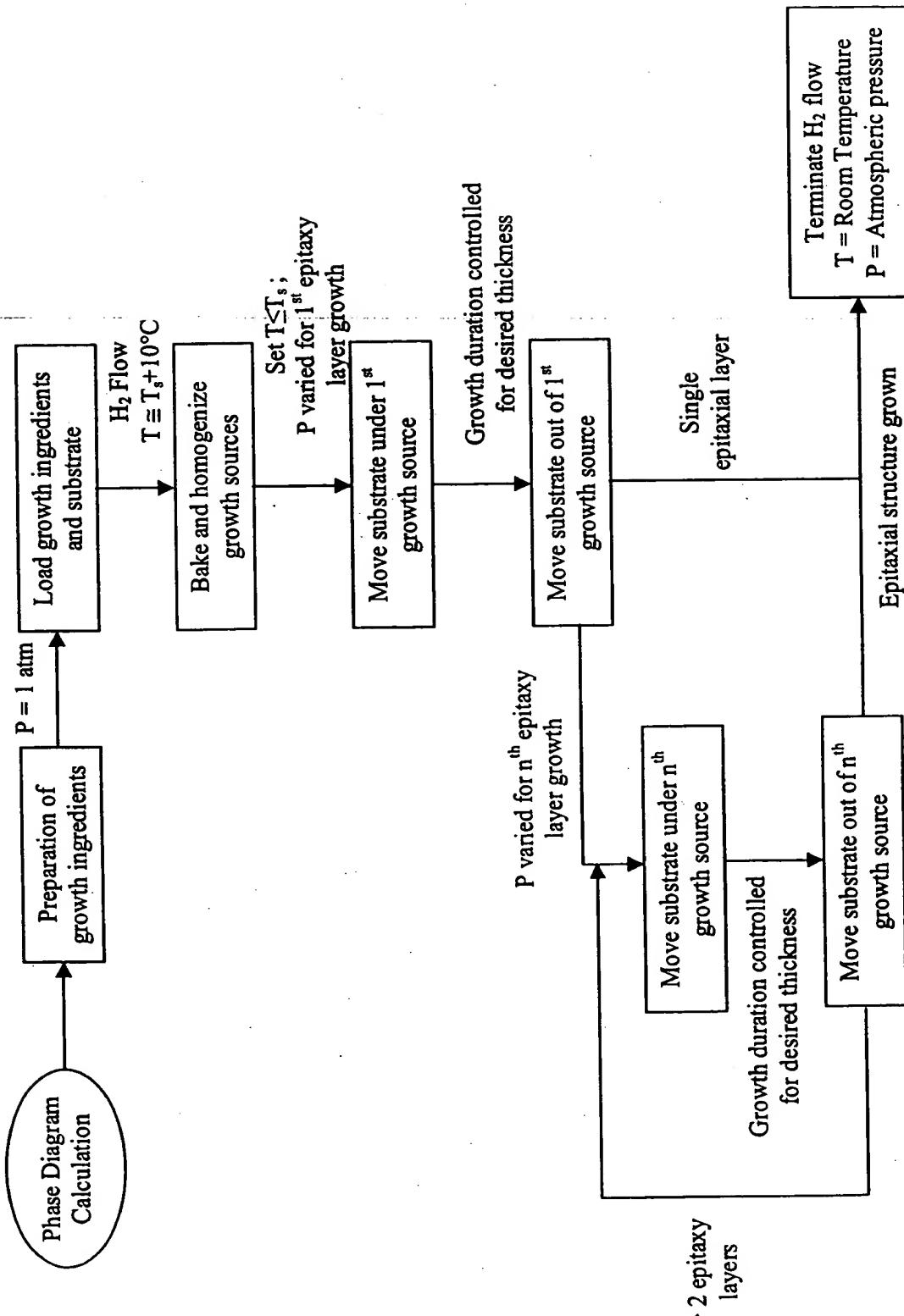
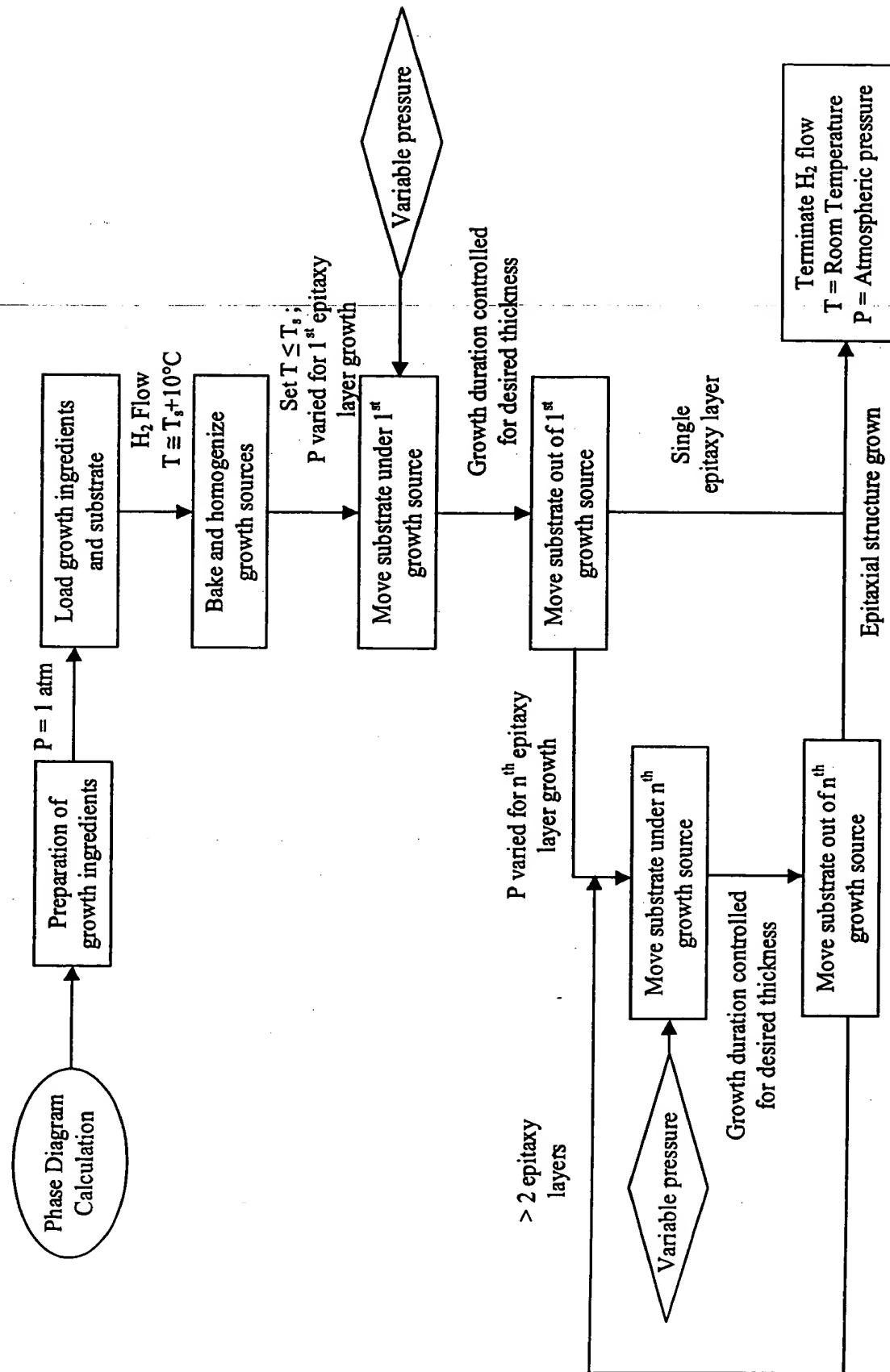


FIGURE 2. Growth of compositional-graded layer

Growth of compositional-graded layer



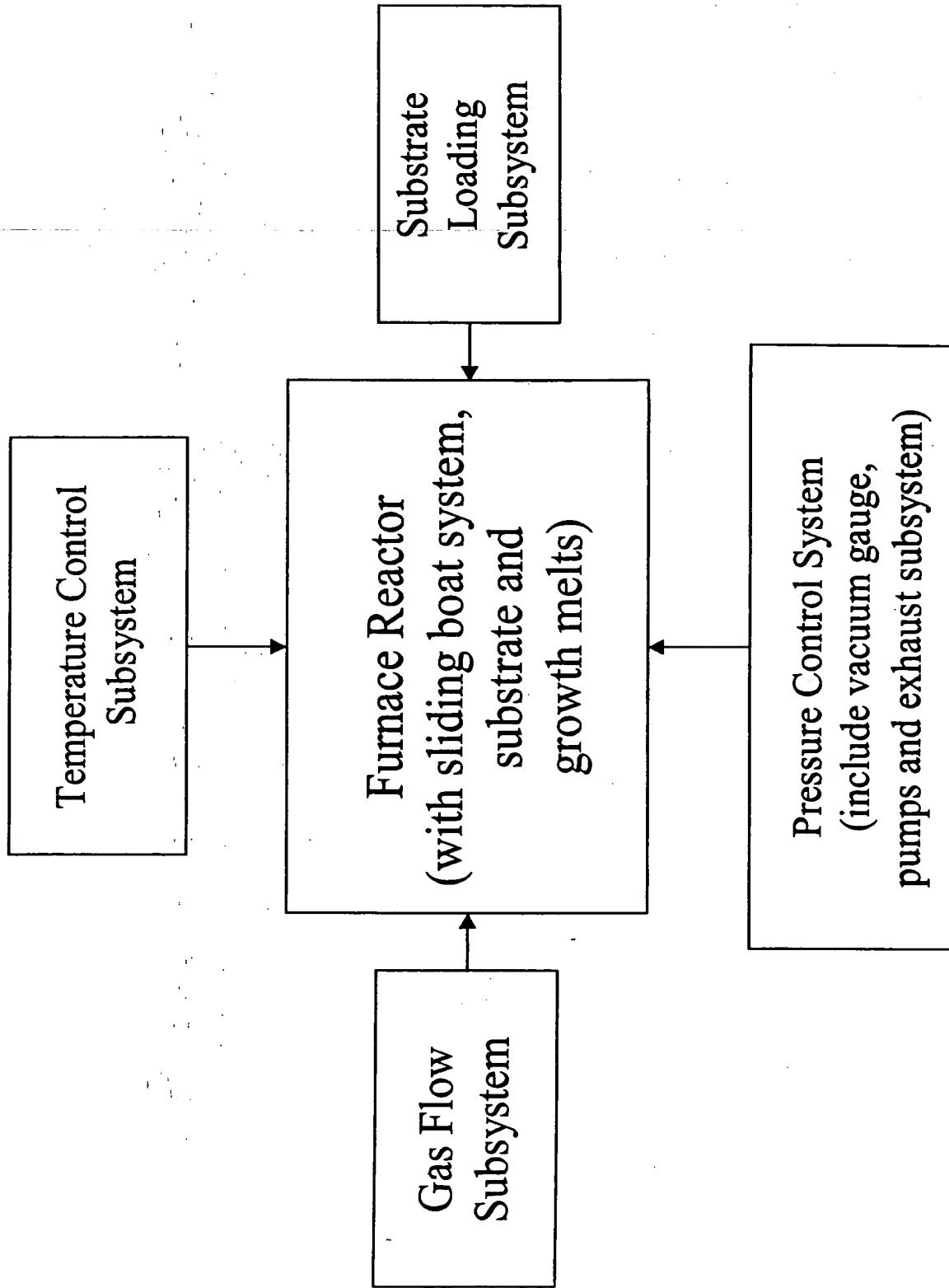
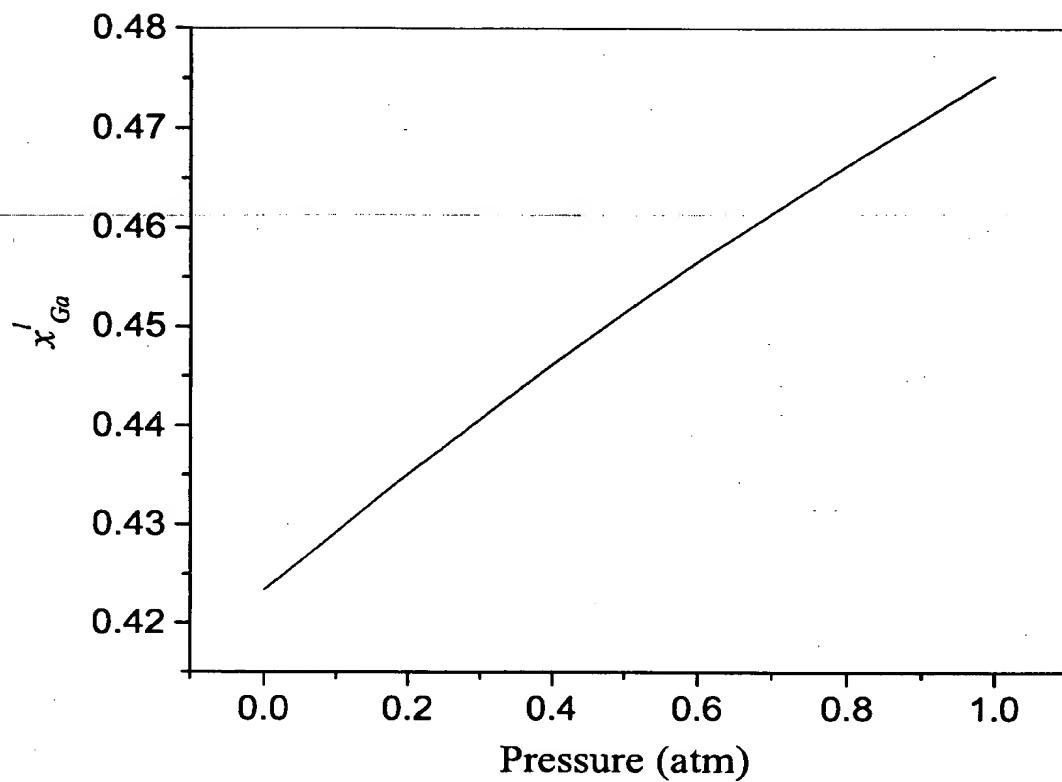
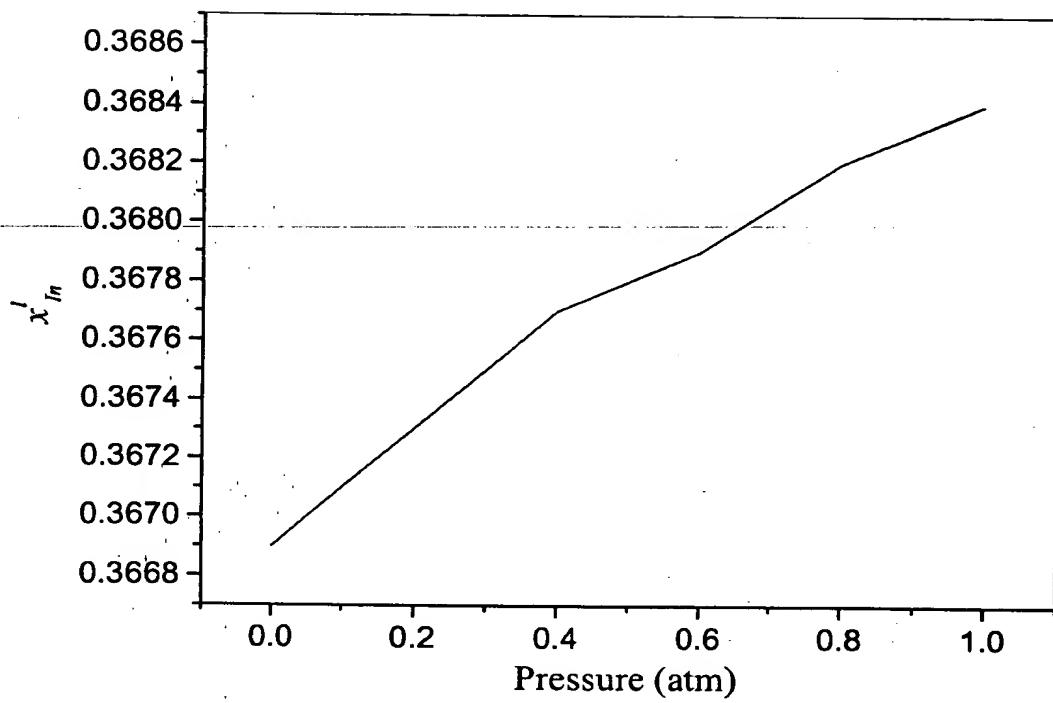


FIGURE 4



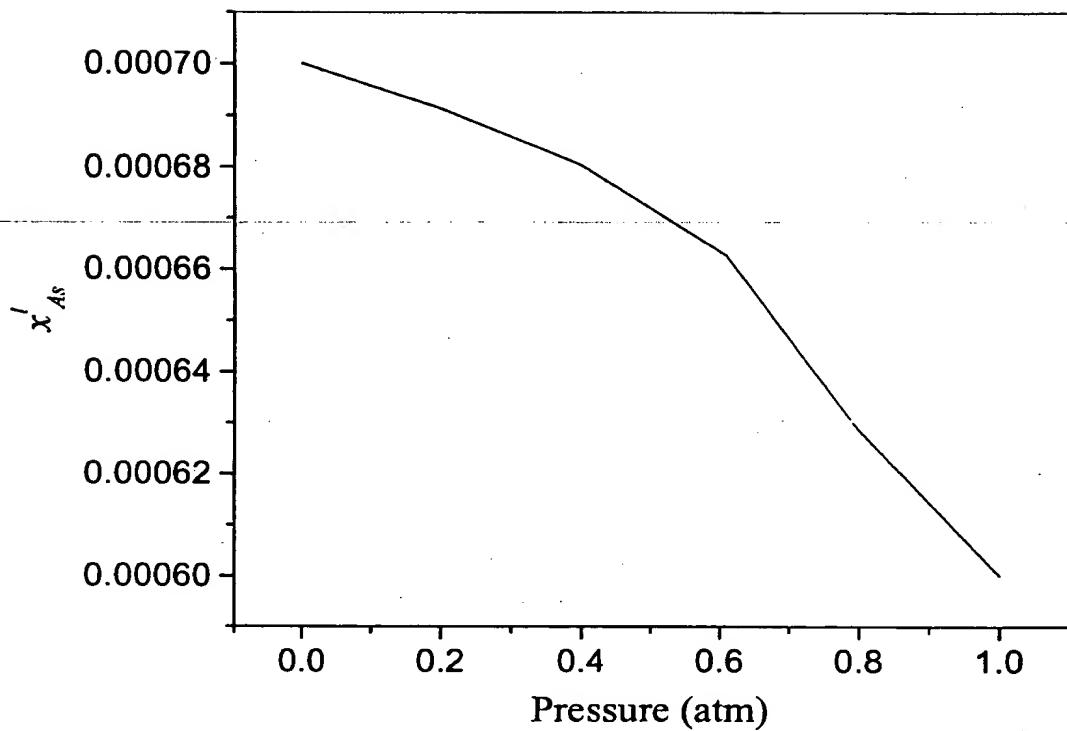
Atomic fraction x'_{Ga} in melt for $\text{In}_{0.1}\text{Ga}_{0.9}\text{As}_{0.087}\text{Sb}_{0.913}$ growth on
GaSb (100) substrate at 550 °C as a function of pressure.

FIGURE 5



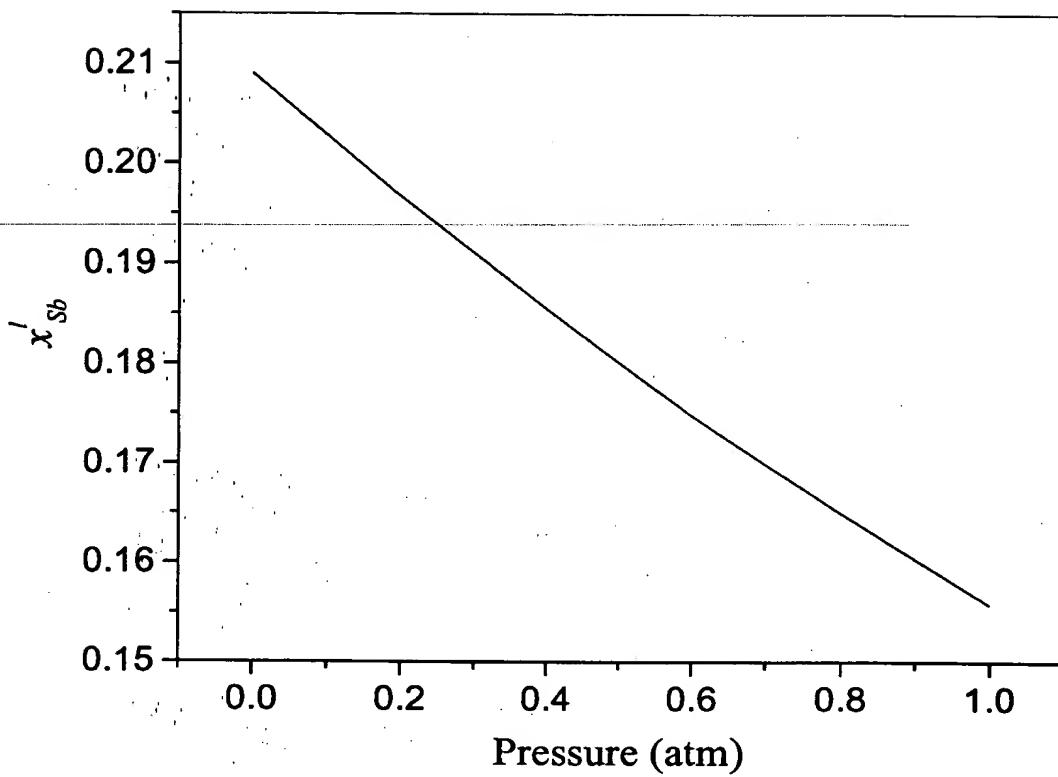
Atomic fraction x'_{In} in melt for $\text{In}_{0.1}\text{Ga}_{0.9}\text{As}_{0.087}\text{Sb}_{0.913}$ growth on
GaSb (100) substrate at 550 °C as a function of pressure.

FIGURE 6



Atomic fraction x'_{As} in melt for $In_{0.1}Ga_{0.9}As_{0.087}Sb_{0.913}$ growth on
GaSb (100) substrate at 550 °C as a function of pressure.

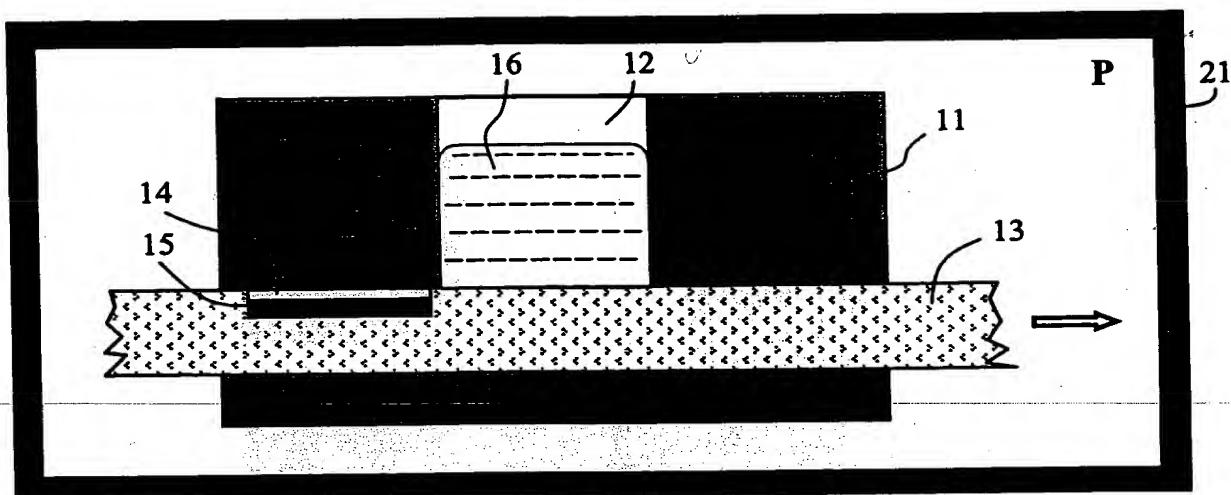
FIGURE 7



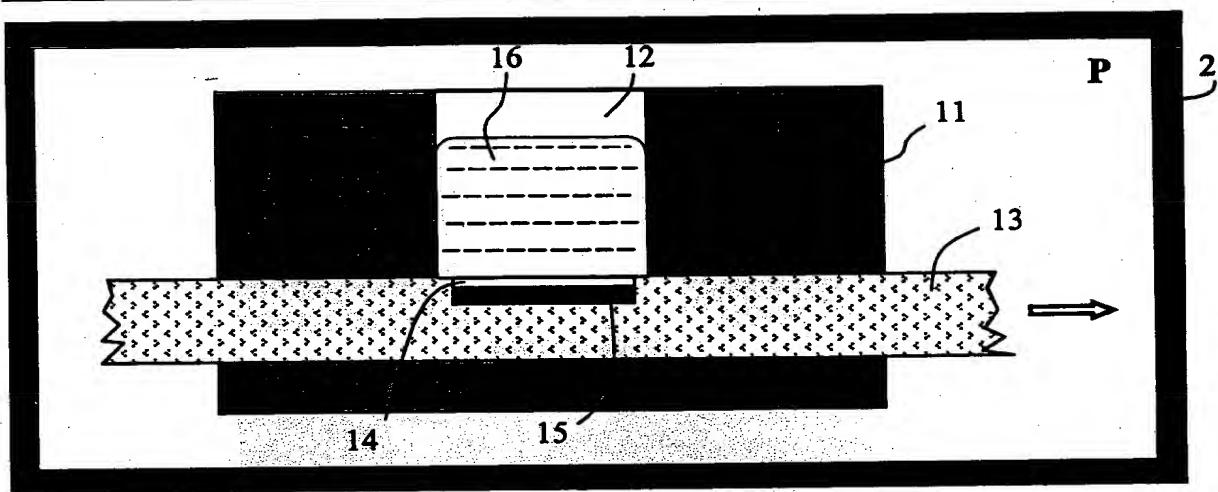
Atomic fraction x'_{Sb} in melt for $\text{In}_{0.1}\text{Ga}_{0.9}\text{As}_{0.087}\text{Sb}_{0.913}$ growth on
GaSb (100) substrate at 550 °C as a function of pressure.

FIGURE 8

(a)



(b)



(c)

